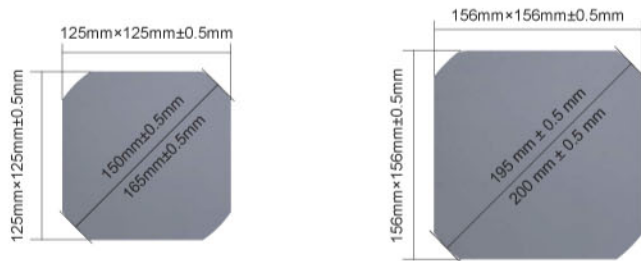


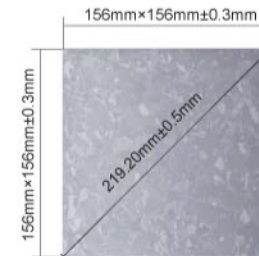
Monocrystalline Silicon Wafer



SPECIFICATIONS

Product	Monocrystalline Silicon Wafer	
Conductivity Type	P-type	
Base Area	125.0mm x 125.0mm ± 0.5mm	156.0mm x 156.0mm ± 0.5mm
Diameter	150.0mm ± 0.5mm; 165.0mm ± 0.5mm	195.0mm ± 0.5mm; 200.0mm ± 0.5mm
Thickness	180 μm ± 20 μm; 200 μm ± 20 μm	
TTV	≤ 30 μm	
Resistivity	0.8-3.0 Ωcm, 3.0-6.0 Ωcm	
Dopant Species	Boron	
Orientation	(100) ± 1°	
Carbon Concentration	≤ 2.5 x 10 ¹⁷ at/cm ³	
Oxygen Concentration	≤ 1 x 10 ¹⁸ at/cm ³	
Dislocation Density	≤ 3,000 / cm ²	
Life Time	≥ 10 μs	
Wafer Surface	As cut and cleaned.No grease stains and pin holes.	
Warping	≤ 50 μm	
Corner Angle	90 ± 0.5 degree	
Edge Chips	Length ≤ 1.0mm,Depth < 0.5mm,No more than 2.	
Edge Cracks	Not allowed	
Saw Marks	Depth ≤ 15 μm	
Pin Holes	No visible pin holes with naked eyes.	

Multicrystalline Silicon Wafer



SPECIFICATIONS

Product	Multicrystalline Silicon Wafer
Conductivity Type	P-type
Base Area	156.0mm x 156.0mm ± 0.3mm
Diameter	219.20mm ± 0.5mm
Thickness	180 μm ± 20 μm; 200 μm ± 20 μm
TTV	≤ 30 μm
Resistivity	0.8-3.0 Ωcm
Dopant Species	Boron
Carbon Concentration	≤ 8 x 10 ¹⁷ at/cm ³
Oxygen Concentration	≤ 7 x 10 ¹⁷ at/cm ³
Life Time	≥ 2 μs
Wafer Surface	As cut and cleaned.No grease stains and pin holes.
Warping	≤ 50 μm
Corner Angle	90 ± 0.2 degree
Edge Chips	Length ≤ 1.0mm,Depth < 0.5mm,No more than 2.
Edge Cracks	Not allowed
Saw Marks	Depth ≤ 15 μm
Pin Holes	No visible pin holes with naked eyes.